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# NTMFS5C628NLT1G

# **ON Semiconductor**

MOSFET TRENCH 6 60V NFET

Any questions, please feel free to contact us. info@kaimte.com

### **Power MOSFET** 60 V, 2.4 mΩ, 150 A, Single N–Channel

#### Features

- Small Footprint (5x6 mm) for Compact Design
- Low R<sub>DS(on)</sub> to Minimize Conduction Losses
- $\bullet \ Low \ Q_G$  and Capacitance to Minimize Driver Losses
- These Devices are Pb-Free and are RoHS Compliant

#### **MAXIMUM RATINGS** (T<sub>J</sub> = $25^{\circ}C$ unless otherwise noted)

Parameter			Symbol	Value	Unit
Drain-to-Source Voltage			V <sub>DSS</sub>	60	V
Gate-to-Source Voltage			V <sub>GS</sub>	±20	V
Continuous Drain		$T_{C} = 25^{\circ}C$	I <sub>D</sub>	150	А
Current R <sub>θJC</sub> (Notes 1, 3)	Steady	T <sub>C</sub> = 100°C		110	
Power Dissipation	State	T <sub>C</sub> = 25°C	PD	110	W
$R_{\theta JC}$ (Note 1)		T <sub>C</sub> = 100°C	1	56	
Continuous Drain		$T_A = 25^{\circ}C$	I <sub>D</sub>	28	А
Current R <sub>θJA</sub> (Notes 1, 2, 3)	Steady State	$T_A = 100^{\circ}C$		20	
Power Dissipation		$T_A = 25^{\circ}C$	PD	3.7	W
R <sub>θJA</sub> (Notes 1 & 2)		$T_A = 100^{\circ}C$		1.9	
Pulsed Drain Current	$T_A = 25^{\circ}C, t_p = 10 \ \mu s$		I <sub>DM</sub>	900	А
Operating Junction and Storage Temperature			T <sub>J</sub> , T <sub>stg</sub>	–55 to +175	°C
Source Current (Body Diode)			۱ <sub>S</sub>	120	А
Single Pulse Drain–to–Source Avalanche Energy ( $I_{L(pk)} = 9 A$ )			E <sub>AS</sub>	565	mJ
Lead Temperature for Soldering Purposes (1/8" from case for 10 s)			ΤL	260	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

#### THERMAL RESISTANCE MAXIMUM RATINGS

Parameter	Symbol	Value	Unit
Junction-to-Case - Steady State	$R_{\theta JC}$	1.3	°C/W
Junction-to-Ambient - Steady State (Note 2)	$R_{\thetaJA}$	40	

1. The entire application environment impacts the thermal resistance values shown, they are not constants and are only valid for the particular conditions noted.

Surface-mounted on FR4 board using a 650 mm<sup>2</sup>, 2 oz. Cu pad.
Maximum current for pulses as long as 1 second is higher but is d

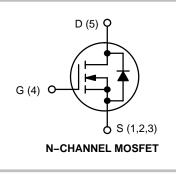
Maximum current for pulses as long as 1 second is higher but is dependent on pulse duration and duty cycle.

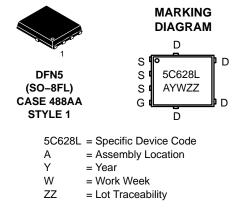


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V <sub>(BR)DSS</sub>	R <sub>DS(ON)</sub> MAX	I <sub>D</sub> MAX	
60 V	2.4 mΩ @ 10 V	150 A	
00 V	3.3 mΩ @ 4.5 V		





#### **ORDERING INFORMATION**

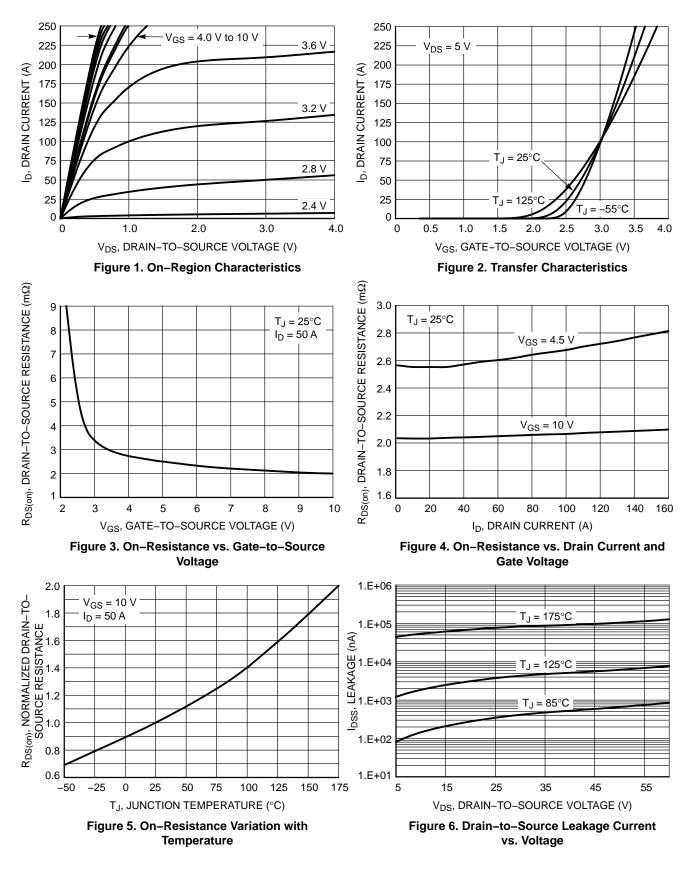
See detailed ordering, marking and shipping information in the package dimensions section on page 5 of this data sheet.

#### **ELECTRICAL CHARACTERISTICS** (T<sub>J</sub> = $25^{\circ}$ C unless otherwise specified)

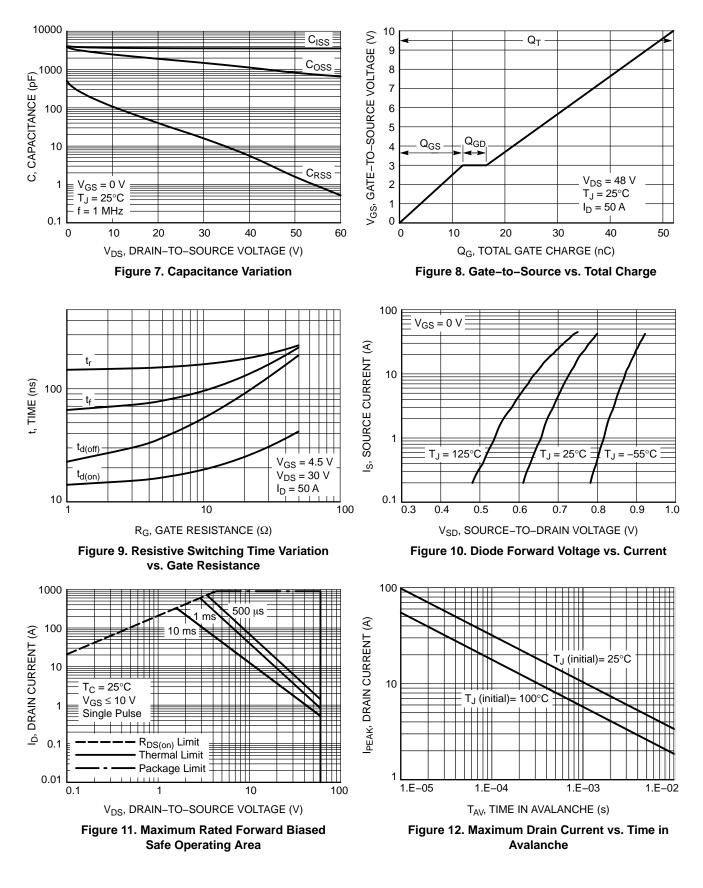
Parameter	Symbol	Test Condition		Min	Тур	Max	Unit
OFF CHARACTERISTICS							
Drain-to-Source Breakdown Voltage	V <sub>(BR)DSS</sub>	$V_{GS} = 0 \text{ V}, \text{ I}_{D} = 250 \mu\text{A}$		60			V
Drain-to-Source Breakdown Voltage Temperature Coefficient	V <sub>(BR)DSS</sub> / T <sub>J</sub>				26		mV/°C
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>GS</sub> = 0 V,	T <sub>J</sub> = 25 °C			10	
		$V_{DS} = 60 V$	T <sub>J</sub> = 125°C			250	μΑ
Gate-to-Source Leakage Current	I <sub>GSS</sub>	$V_{DS} = 0 V, V_{G}$	<sub>S</sub> = 20 V			100	nA
ON CHARACTERISTICS (Note 4)	•						
Gate Threshold Voltage	V <sub>GS(TH)</sub>	$V_{GS} = V_{DS}, I_{D} = 135 \mu A$		1.2		2.0	V
Threshold Temperature Coefficient	V <sub>GS(TH)</sub> /T <sub>J</sub>				-5.0		mV/°C
Drain-to-Source On Resistance	R <sub>DS(on)</sub>	V <sub>GS</sub> = 10 V	I <sub>D</sub> = 50 A		2.0	2.4	_
		V <sub>GS</sub> = 4.5 V	I <sub>D</sub> = 50 A		2.6	3.3	mΩ
Forward Transconductance	9FS	V <sub>DS</sub> = 15 V, I	<sub>D</sub> = 50 A		110		S
CHARGES AND CAPACITANCES							
Input Capacitance	C <sub>ISS</sub>	V <sub>GS</sub> = 0 V, f = 1 MHz, V <sub>DS</sub> = 25 V			3600		pF
Output Capacitance	C <sub>OSS</sub>				1700		
Reverse Transfer Capacitance	C <sub>RSS</sub>				28		
Total Gate Charge	Q <sub>G(TOT)</sub>	V <sub>GS</sub> = 4.5 V, V <sub>DS</sub> = 48 V; I <sub>D</sub> = 50 A			24		
Total Gate Charge	Q <sub>G(TOT)</sub>	V <sub>GS</sub> = 10 V, V <sub>DS</sub> = 48 V; I <sub>D</sub> = 50 A			52		
Threshold Gate Charge	Q <sub>G(TH)</sub>	V <sub>GS</sub> = 4.5 V, V <sub>DS</sub> = 48 V; I <sub>D</sub> = 50 A			6.0		nC
Gate-to-Source Charge	Q <sub>GS</sub>				12		
Gate-to-Drain Charge	Q <sub>GD</sub>				4.5		
Plateau Voltage	V <sub>GP</sub>				3.0		V
SWITCHING CHARACTERISTICS (Note 5	5)						
Turn–On Delay Time	t <sub>d(ON)</sub>	$V_{GS}$ = 4.5 V, $V_{DS}$ = 30 V, I <sub>D</sub> = 50 A, R <sub>G</sub> = 2.5 Ω			15		
Rise Time	t <sub>r</sub>				150		ns
Turn–Off Delay Time	t <sub>d(OFF)</sub>				28		
Fall Time	t <sub>f</sub>				70		
DRAIN-SOURCE DIODE CHARACTERIS	TICS						
Forward Diode Voltage	V <sub>SD</sub>	$V_{GS} = 0 V$ , $T_J = 25^{\circ}C$			0.8	1.2	
	VGS -	$I_{\rm S} = 50 \rm{A}$	T <sub>J</sub> = 125°C		0.75		V
Reverse Recovery Time	t <sub>RR</sub>	V <sub>GS</sub> = 0 V, dls/dt = 100 A/μs, I <sub>S</sub> = 50 A			55		
Charge Time	ta				28		ns
Discharge Time	t <sub>b</sub>				28		
Reverse Recovery Charge	Q <sub>RR</sub>				60		nC

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions. 4. Pulse Test: pulse width  $\leq 300 \ \mu$ s, duty cycle  $\leq 2\%$ . 5. Switching characteristics are independent of operating junction temperatures.

#### **TYPICAL CHARACTERISTICS**



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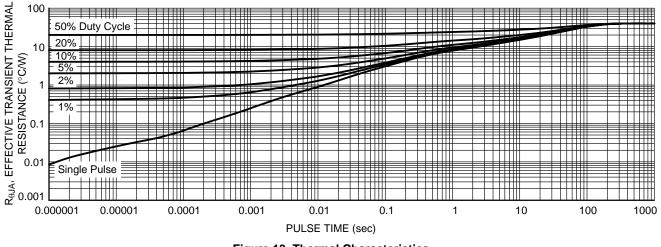


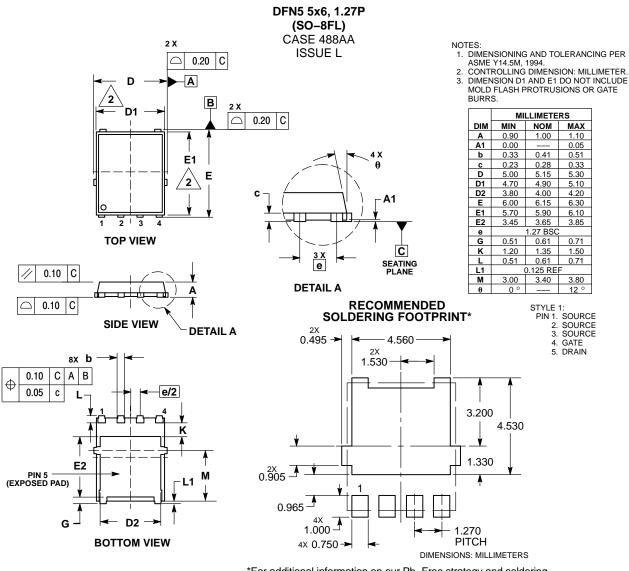
Figure 13. Thermal Characteristics

#### **DEVICE ORDERING INFORMATION**

Device	Marking	Package	Shipping <sup>†</sup>
NTMFS5C628NLT1G	5C628L	DFN5 (Pb–Free)	1500 / Tape & Reel
NTMFS5C628NLT3G	5C628L	DFN5 (Pb–Free)	5000 / Tape & Reel

+For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

#### PACKAGE DIMENSIONS



\*For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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